

NCE N-Channel Enhancement Mode Power MOSFET



The NCE3065K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

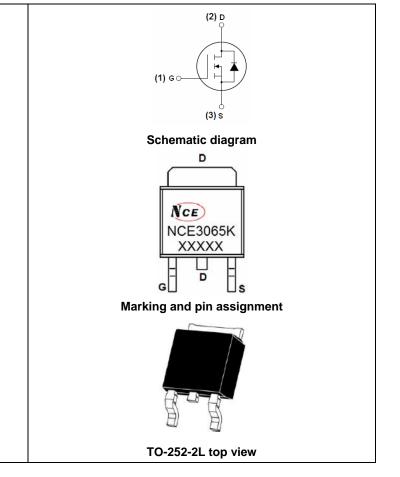
General Features

- V_{DS} =30V,I_D =65A
 - R_{DS(ON)} <7.0mΩ @ V_{GS}=10V
 - $R_{DS(ON)} < 9.5m\Omega @ V_{GS}=5V$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3065K	NCE3065K	TO-252-2L	-	-	-

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	65	A
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	46	А
Pulsed Drain Current	I _{DM}	200	A
Maximum Power Dissipation	PD	65	W
Derating factor		0.43	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	150	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	2.3	°C/W	1
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Electrical Characteristics (TC=25 $^\circ\!\!\mathrm{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics	·						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	·						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.5	2.5	V	
Drain-Source On-State Resistance		V _{GS} =10V, I _D =20A	-	5.7	7.0	m0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	7.7	9.5	mΩ	
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	20	-	-	S	
Dynamic Characteristics (Note4)	·						
Input Capacitance	C _{lss}		-	1400	-	PF	
Output Capacitance	C _{oss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	205	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	177	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	9	-	nS	
Turn-on Rise Time	tr	V _{DD} =5V,I _D =20A	-	8	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =6 Ω	-	28	-	nS	
Turn-Off Fall Time	t _f		-	5	-	nS	
Total Gate Charge	Qg		-	32.3	-	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =20A, V _{GS} =10V	-	4.9	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	6.9	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	0.85	1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	65	А	
Reverse Recovery Time	t _{rr}	TJ = 25°C, I _F = 20A	-	-	27	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	-	20	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negl	igible (turi	n-on is do	ominated b	y LS+LD)	

Notes:

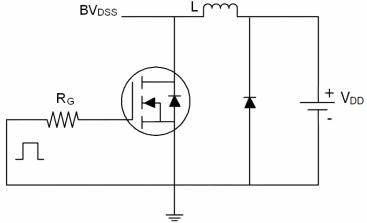
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: $Tj=25^{\circ}C$, $V_{DD}=15V$, $V_{G}=10V$, L=0.5mH, $Rg=25\Omega$



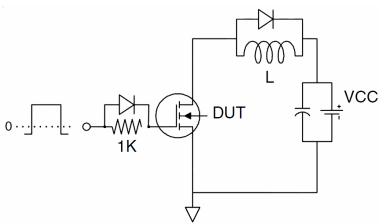
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Test Circuit

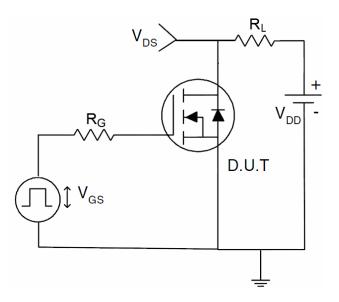
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit

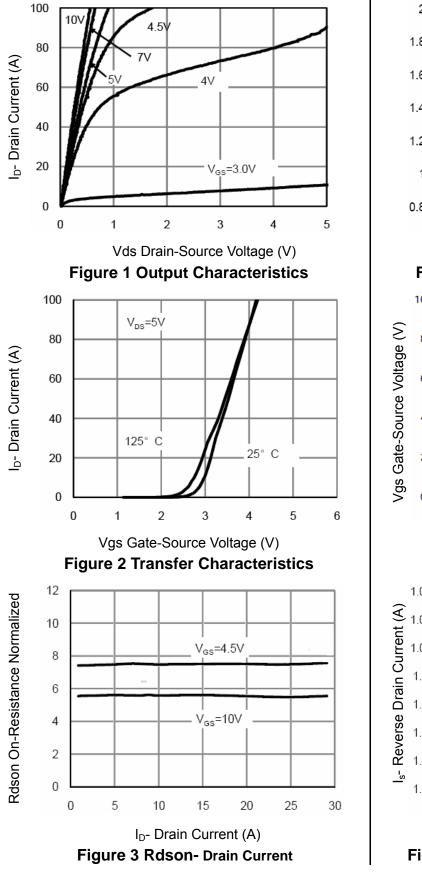


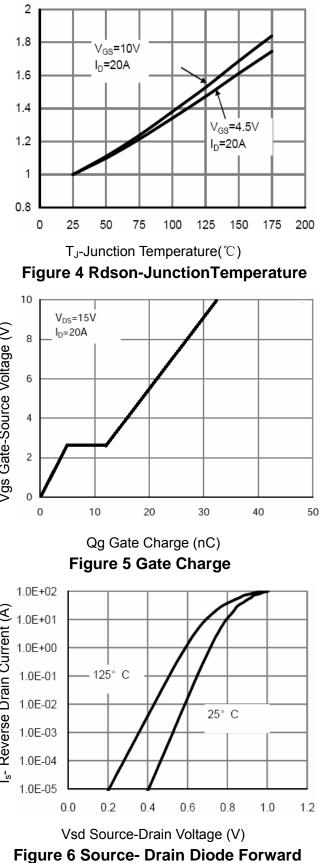
3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)







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NCE3065K

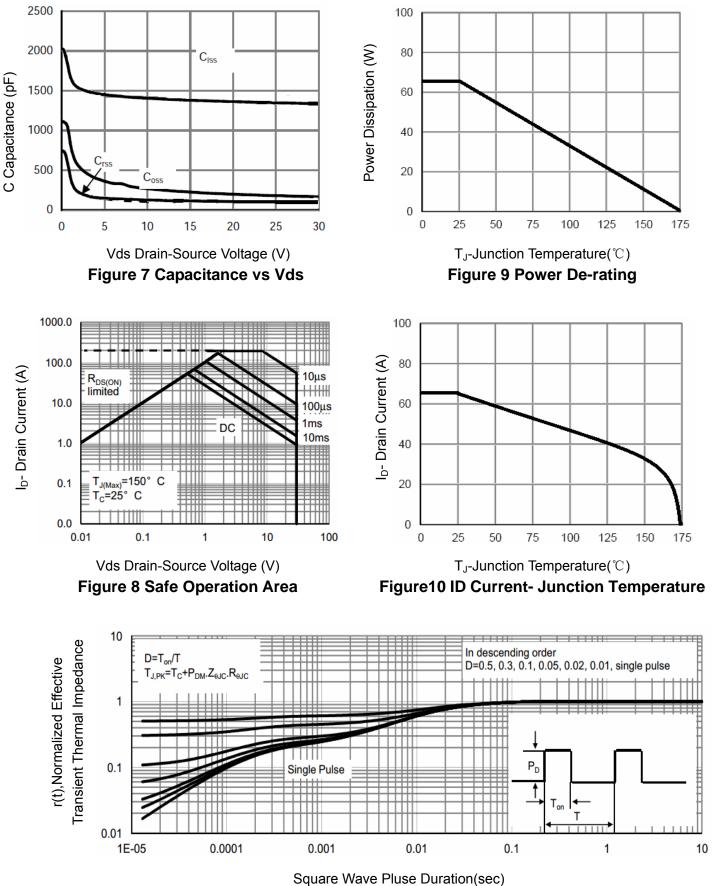
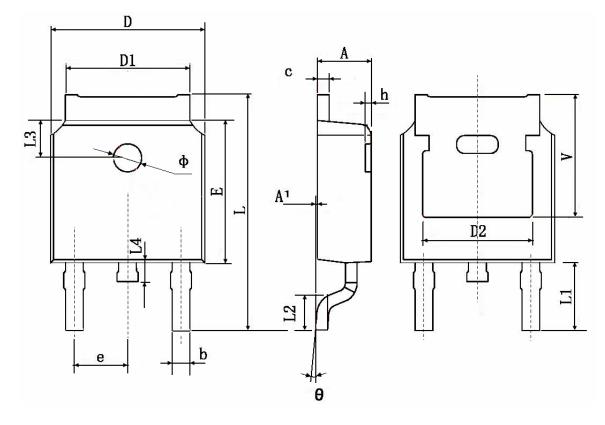


Figure 11 Normalized Maximum Transient Thermal Impedance

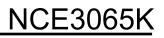


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TO-252 Package Information



Querrale al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	D TYP.	0.211 TYP.		



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